

N-Channel Super Junction Power MOSFET IV

General Description

The series of devices use advanced trench gate super junction technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. This super junction MOSFET fits the industry's AC-DC SMPS requirements for PFC, AC/DC power conversion, and industrial power applications.

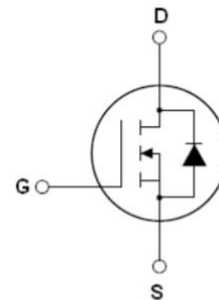
Features

- Optimized body diode reverse recovery performance
- Low on-resistance and low conduction losses
- Small package
- Ultra Low Gate Charge cause lower driving requirements
- 100% Avalanche Tested
- ROHS compliant

Application

- Power factor correction (PFC)
- Switched mode power supplies(SMPS)
- Uninterruptible Power Supply (UPS)
- LLC Half-bridge

$V_{DS \min @ T_{jmax}}$	550	V
$R_{DS(ON)TYP.}$	150	m Ω
I_D	17	A
Q_g	22	nC



Schematic diagram

✧ Intrinsic fast-recovery body diode

Package Marking And Ordering Information

Device	Device Package	Marking
NCE50NF180D	TO-263-2L	NCE50NF180D



TO-263

Table 1. Absolute Maximum Ratings ($T_c=25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Drain-Source Voltage ($V_{GS}=0V$)	V_{DS}	500	V
Gate-Source Voltage ($V_{DS}=0V$), AC ($f>1\text{ Hz}$)	V_{GS}	± 30	V
Gate-Source Voltage ($V_{DS}=0V$), DC	V_{GS}	± 20	V
Continuous Drain Current at $T_c=25^\circ\text{C}$	$I_{D(DC)}$	17	A
Continuous Drain Current at $T_c=100^\circ\text{C}$	$I_{D(DC)}$	11.9	A
Pulsed drain current (Note 1)	$I_{DM}(\text{pluse})$	51	A
Maximum Power Dissipation ($T_c=25^\circ\text{C}$)	P_D	129	W
Derate above 25°C		0.86	W/ $^\circ\text{C}$
Single pulse avalanche energy (Note 2)	E_{AS}	62.5	mJ
Single pulse avalanche current (Note 2)	I_{AS}	5	A
Repetitive Avalanche energy, t_{AR} limited by T_{jmax} (Note 1)	E_{AR}	0.54	mJ
Reverse diode dv/dt , $V_{DS} \leq 400\text{ V}$, $I_{SD} < I_D$	dv/dt	15	V/ns
Drain Source voltage slope, $V_{DS} \leq 400\text{ V}$	dv/dt	50	V/ns
Operating Junction and Storage Temperature Range	T_J, T_{STG}	$-55...+175$	$^\circ\text{C}$

Table 2. Thermal Characteristic

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case (Maximum)	R_{thJC}	1.16	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction-to-Ambient (Maximum)	R_{thJA}	62	$^{\circ}\text{C}/\text{W}$

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
On/off states						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250uA	500			V
Zero Gate Voltage Drain Current(Tc=25℃)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			10	μA
Zero Gate Voltage Drain Current(Tc=125℃)	I _{DSS}	V _{DS} =500V,V _{GS} =0V			300	μA
Gate-Body Leakage Current	I _{GSS}	V _{GS} =±20V,V _{DS} =0V			±200	nA
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250uA	3		5	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8.5A		150	180	mΩ
Dynamic Characteristics						
Gate Resistance	R _g	F=1MHZ, D-S short		18		Ω
Input Capacitance	C _{iss}	V _{DS} =50V,V _{GS} =0V, F=1MHz		1157		pF
Output Capacitance	C _{oss}			52		pF
Reverse Transfer Capacitance	C _{rss}			4.8		pF
Total Gate Charge	Q _g	V _{DS} =400V,I _D =8.5A, V _{GS} =10V		22		nC
Gate-Source Charge	Q _{gs}			9.1		nC
Gate-Drain Charge	Q _{gd}			5.1		nC
Gate plateau voltage	V _{gp}			6.6		V
Switching times						
Turn-on Delay Time	t _{d(on)}	V _{DD} =400V,I _D =8.5A, R _G =4Ω,V _{GS} =10V		12		nS
Turn-on Rise Time	t _r			10		nS
Turn-Off Delay Time	t _{d(off)}			56		nS
Turn-Off Fall Time	t _f			8		nS
Source- Drain Diode Characteristics						
Source-drain current(Body Diode)	I _{SD}	T _C =25℃			17	A
Pulsed-Source-drain current(Body Diode)	I _{SDM}				51	A
Forward on voltage	V _{SD}	T _j =25℃,I _{SD} =17A,V _{GS} =0V		0.9	1.1	V
Reverse Recovery Time	t _{rr}	T _j =25℃,I _f =8.5A, di/dt=100A/μs		165		nS
Reverse Recovery Charge	Q _{rr}			0.83		uC
Peak reverse recovery current	I _{rrm}			10		A

Notes: 1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. $T_j=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, R_G=25\Omega$

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS (curves)

Figure1. Safe operating area

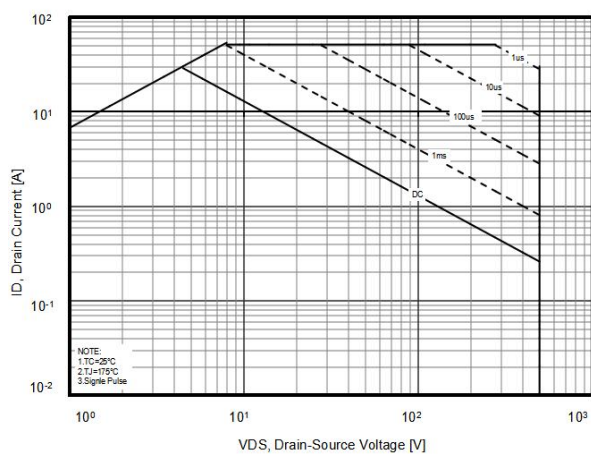


Figure2. Source-Drain Diode Forward Voltage

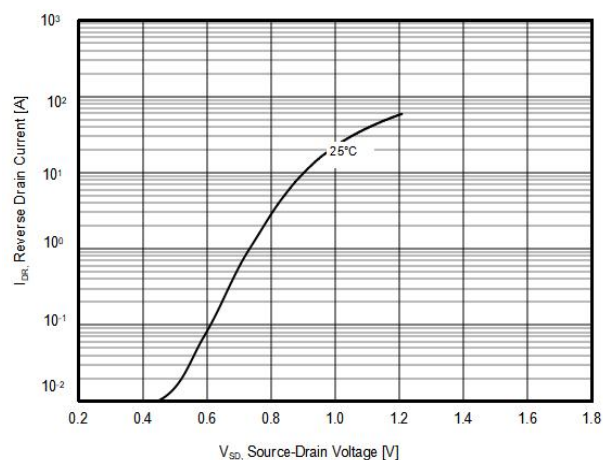


Figure3. Output characteristics

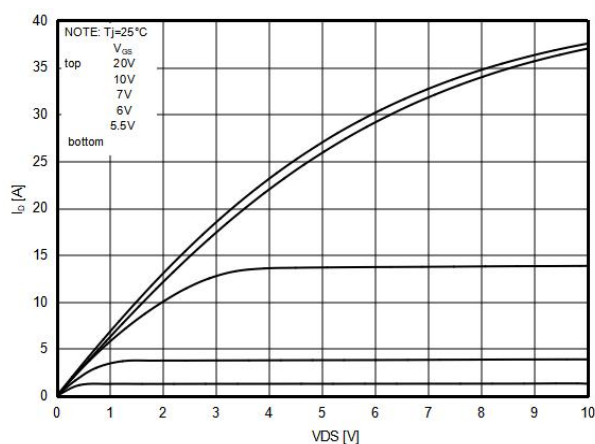


Figure4. Transfer characteristics

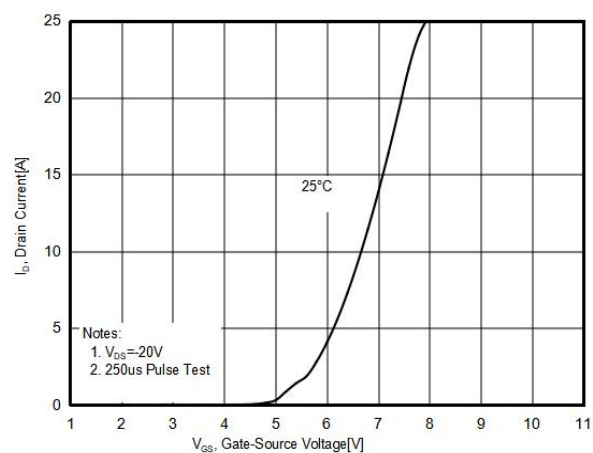


Figure5. Static drain-source on resistance

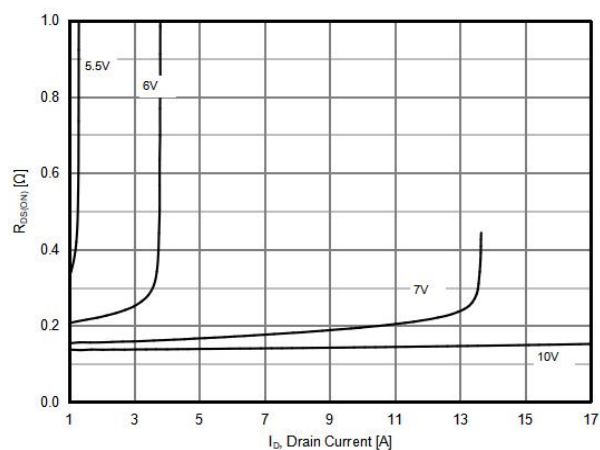


Figure6. $R_{DS(on)}$ vs Junction Temperature

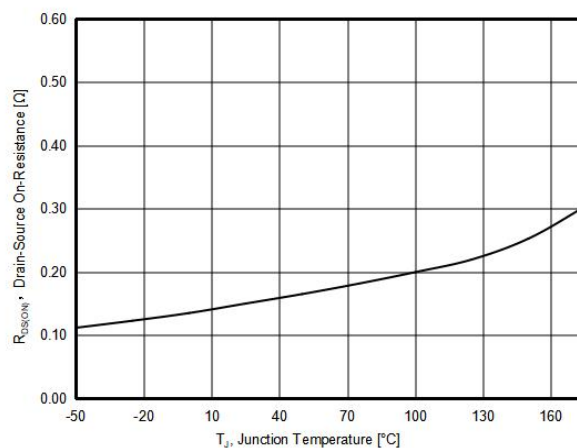


Figure7. BV_{DS} vs Junction Temperature

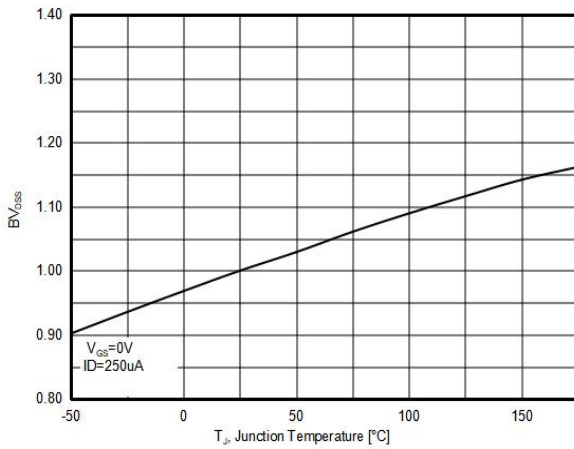


Figure8. Maximum I_D vs Junction Temperature

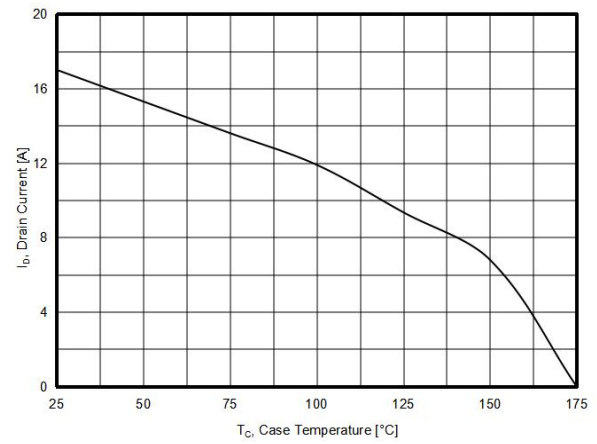


Figure9. Gate charge waveforms

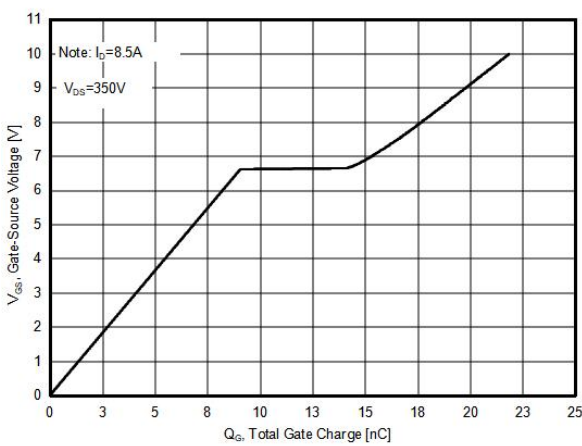
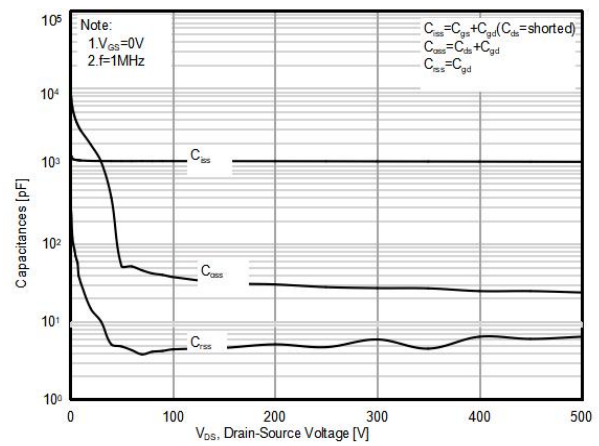
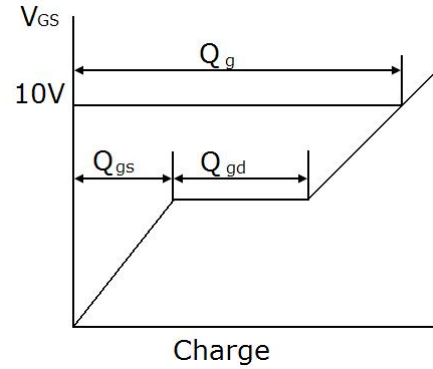
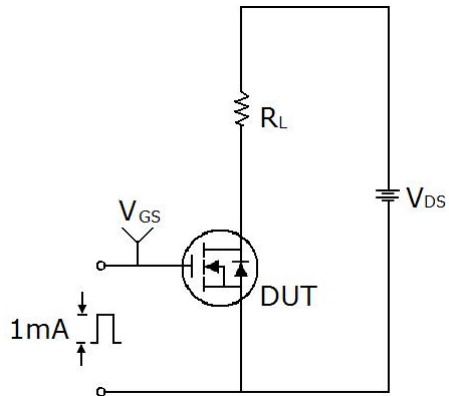


Figure10. Capacitance

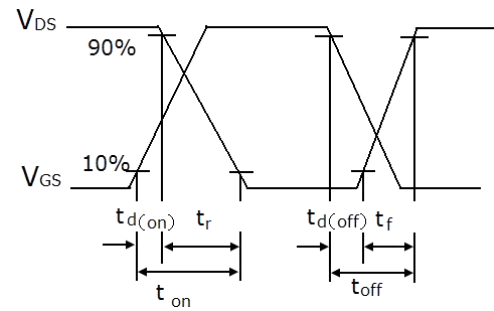


Test circuit

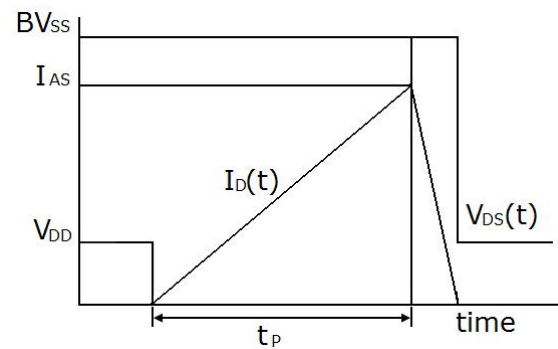
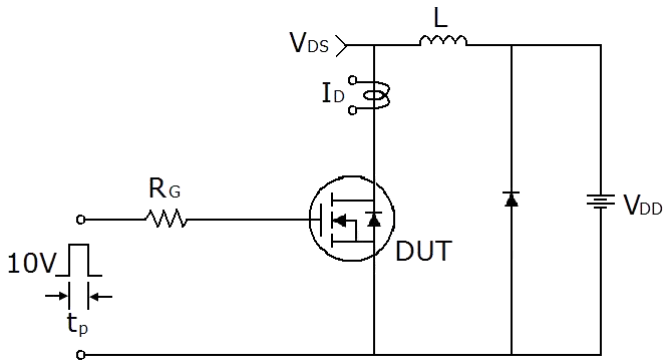
1) Gate charge test circuit & Waveform



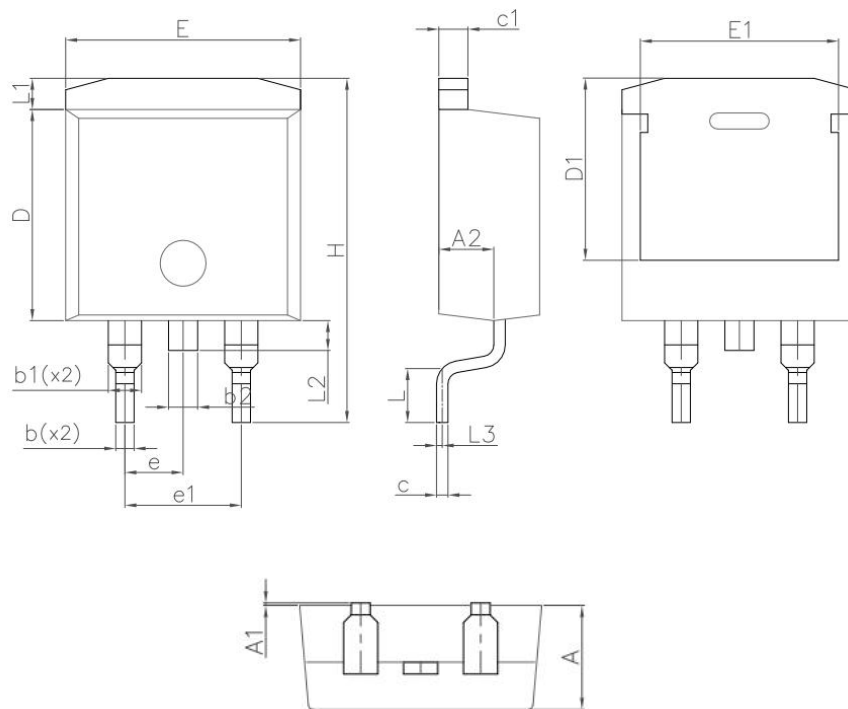
2) Switch Time Test Circuit:



3) Unclamped Inductive Switching Test Circuit & Waveforms



TO-263-E Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.20	4.60	0.165	0.181
A1	0.00	0.25	0.00	0.010
A2	2.20	2.60	0.087	0.102
b	0.70	0.90	0.028	0.035
b1	1.20	1.75	0.047	0.069
b2	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
c1	1.15	1.40	0.045	0.055
D	9.10	9.30	0.358	0.366
D1	7.63	8.23	0.300	0.324
E	10.05	10.45	0.396	0.411
E1	8.35	8.95	0.329	0.352
e	2.54BSC		0.100BSC	
e1	5.08BSC		0.200BSC	
H	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.36REF		0.054REF	
L2	1.30REF		0.051REF	

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